















Radiation damage caused by neutron capture in boron doped silicon pixel sensors

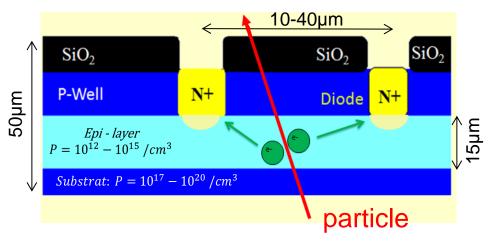
Benjamin Linnik

6.9.2016
Institut für Kernphysik, Goethe University, Frankfurt am Main



The question:



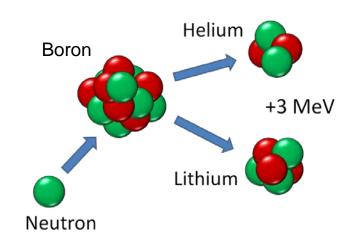


CMOS Monolithic Active Pixel Sensors

- Are being optimized to tolerate extremely high radiation doses (ionizing and non-ionizing).
- Base typically on P-doped silicon
- => Contains Boron

Boron (10B) is known to:

- Capture thermal neutrons with huge cross section (~1000 b)
- Decay n+¹⁰B => ⁷Li + ⁴He + 3 MeV
- ⇒ Fast ions are created in Si
- ⇒ Additional bulk damage is created



Does ¹⁰B cause sizable additional radiation damage w.r.t standard NIEL model?

Theoretical estimate

National Nuclear Data Center

 $10^{-5} 10^{-4} 10^{-3} 10^{-2} 10^{-1} 10^{0} 10^{1} 10^{2} 10^{3} 10^{4} 10^{5} 10^{6} 10^{7}$

Energie [eV]

10⁴

10³

10²

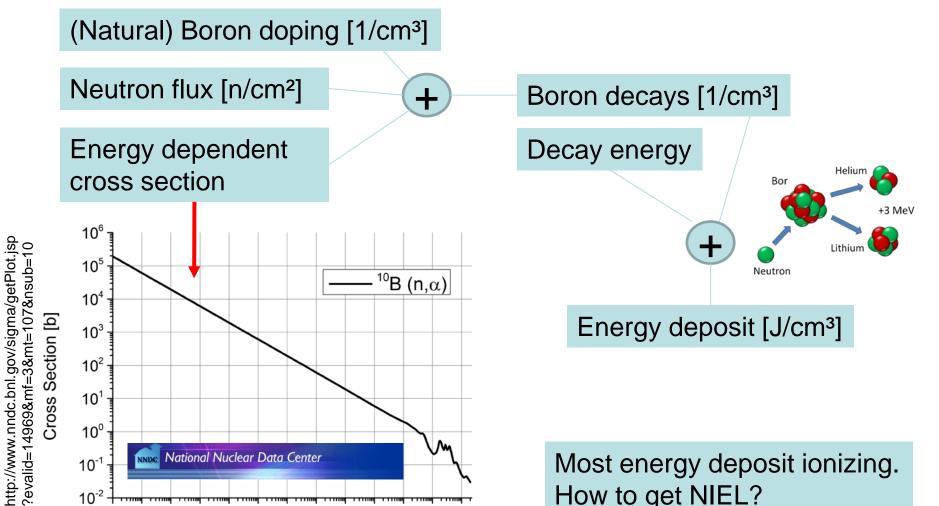
10¹

10°

10⁻¹

Cross Section [b]





Most energy deposit ionizing. How to get NIEL?

Energy deposit [J/cm³]

From ion energy to NIEL



Idea: Compare number of vacancies:

caused by fission ions (unknown hardness factor)

caused by protons (known hardness factor)

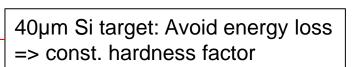
Tool: SRIM (software and references: www.srim.org)

Simulates flight of ions in matter (~MeV energies)

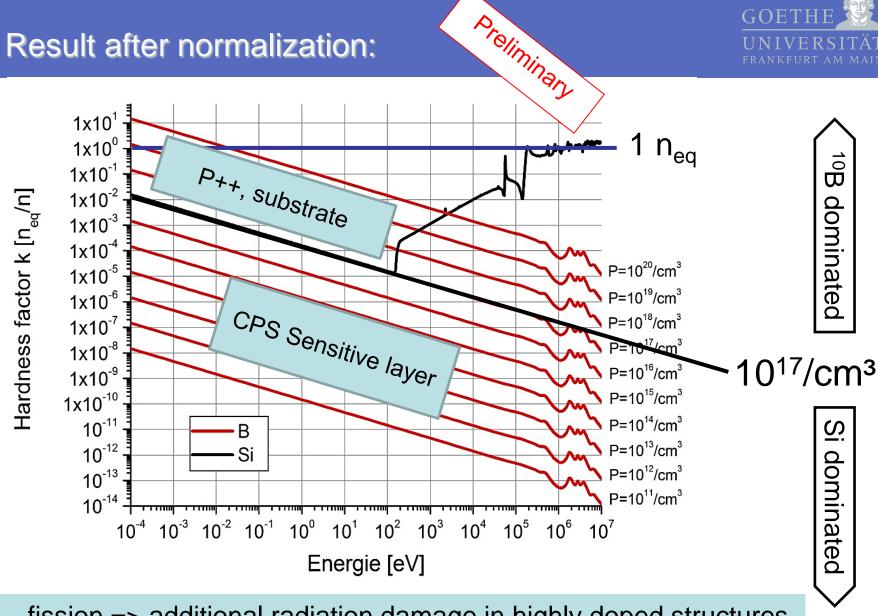
⇒ Simulate vacancies cause by p, ⁴He and ⁷Li

Results:

	Vacancies	
p (30 MeV)	0.7 / 40μm 🔸	
⁴ He	277 / ion	
⁷ Li	613 / ion	



Depth vs. Y-Axis	\mathbf{l}
- 7 /- /	l
-	ļ
-	+
	t
	t
- File	t
, le et l	I
- Le k f p T	
0 A Target Depth 10 ur	n



¹⁰B – fission => additional radiation damage in highly doped structures

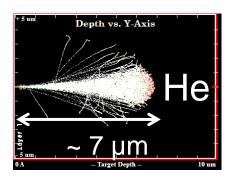
Benjamin Linnik Pixel 2016 4

Why does it matter?



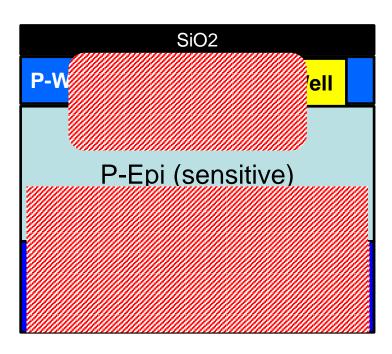
In first order:

- Lowly doped sensitive volume not affected
- lons are created in highly doped volumes.





Penetration depth of ions (SRIM)



Possible damage mechanism:

- lons are created in P++
- Ions enter sensitive volume, create sizable (?) damage here

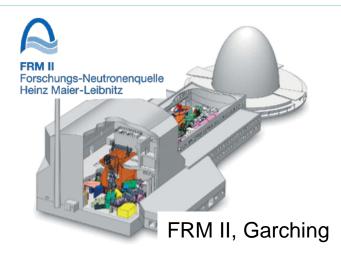
Likely:

- Only part of sensitive volume affected
- "Effective" hardness factor depending on sensor geometry, etc...

Getting experimental



Idea: Compare radiation damage cause by fast and cold neutrons



MEDAPP

- Direct ²³⁵U fission neutrons
- 99% of all neutrons >100 keV
- Ionizing dose: <100 krad/10¹³n_{eq}/cm²

PGAA

- Cold neutrons 1.8 x 10⁻³ eV
- Ionizing dose: Unknown



Sensor: MIMOSA-19, IPHC, Strasbourg

- Design: AMS 0.35 LR, Year 2006 (outdated design)
- Pixel: 12 µm pitch, L-shaped diode
- Doping assumption: $\sim 10^{15} \ (epi)$, $\sim 10^{19} (substrate)$ => Not depleted, charge collection by diffusion
- Feature: 3T-pixel, easy acces to I_{Leakage}

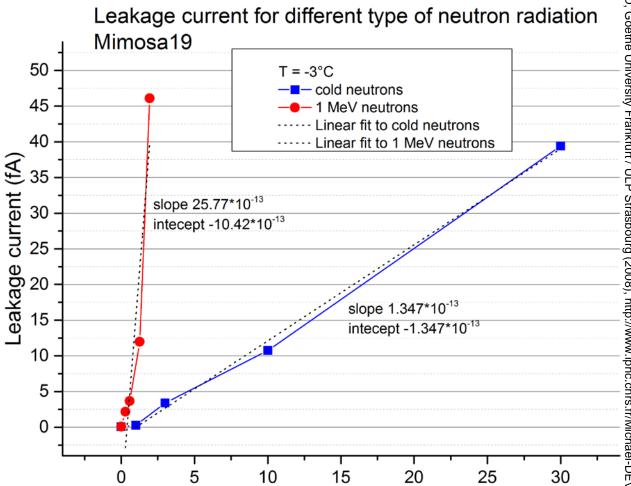
Observables: CCE, diode leakage current

Results: Comparision of leakage current



Slopes suggest:

$$1 n_{cold} \approx 7.5 \times 10^{-2} n_{eq}$$



Dose (10¹³ n/cm²)

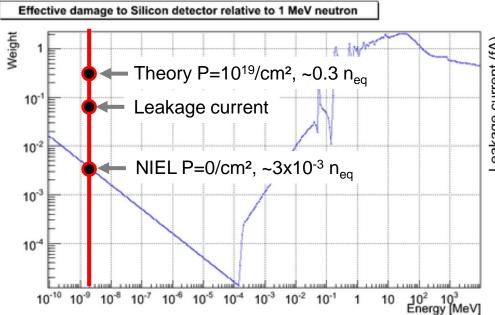
Measurement procedure:M. Deveaux, "radiation hardness studies on Monolithic Active Pixel Sensors", PhD, Goethe University Frankfurt / ULP Strasbourg (2008), http://www.iphc.cnrs.fr/Michael-DEVEAUX.htm

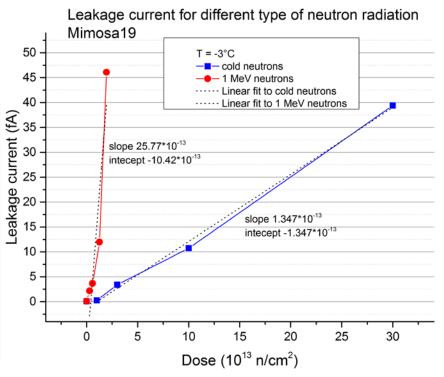




Slopes suggest:

 $1 n_{cold} \approx 7.5 \times 10^{-2} n_{eq}$





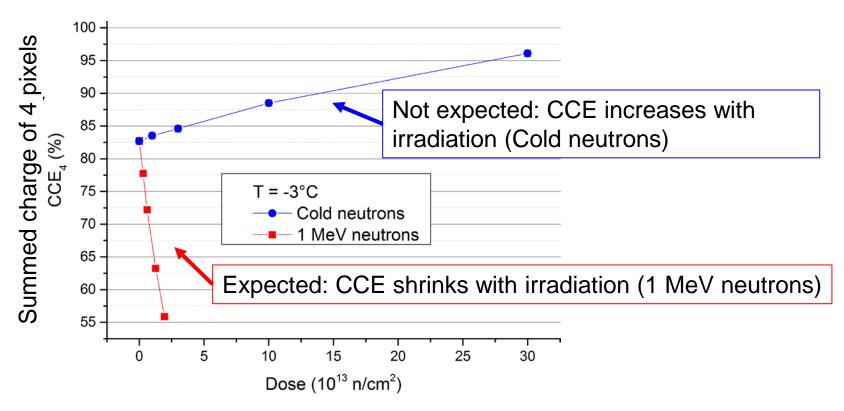
Observation compatible with theoretical expectation but:

- Potential bias by parasitic γ-doses.
- Next step: Try to eliminate surface damage by annealing
- Work in progress, not yet conclusive => Stay tuned

Experimental results: CCE

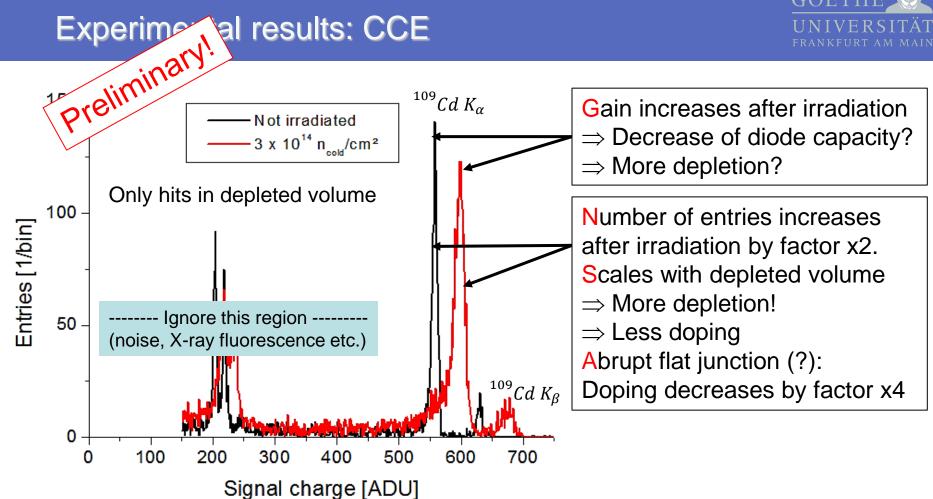


Sensor illuminated with ¹⁰⁹Cd (22.1 keV X-ray), detect clusters



Response differs fundamentally between cold \Leftrightarrow 1MeV Neutrons Effective hardness factor cannot be extracted





Potential explaination:

Intense acceptor removal (factor x4 from P=10¹⁵/cm³)

- ⇒ Additional depletion improves CCE, dominates trapping
- ! No significant acceptor removal observed with 1 MeV neutrons for <2x10¹³n_{eg}/cm²





Does ¹⁰B fission cause sizable rad. damage in P-doped Si?

Theoretical estimate:

- P>10¹⁷/cm³ => Expect additional damage w.r.t standard NIEL curve
- Fission ions may damage lowly doped silicon indirectly due to 7µm range

Experimental study (MIMOSA-19, ~10¹⁵/cm³ epi layer, ~10¹⁹/cm³ substrate):

Observation:

- Leakage currents:
 - Cold neutron cause factor ~20 more damage than according to standard NIEL
 - Risk of sizeable bias due to parasitic ionizing doses (work in progress)
- CCE:
 - Cold neutrons cause strong acceptor removal, CCE increases
 - Acceptor removal exceeds finding for 2x10¹³n_{eq}/cm² (1MeV)

Preliminary conclusion (of a not-yet-fully-conclusive study):

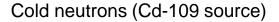
- 10B fission seems to cause rad. damage beyond standard NIEL
- Plausibly no risk for vertex detectors (dominated by direct radiation)
- Risk of unexpected effects in case of high thermal neutron doses.

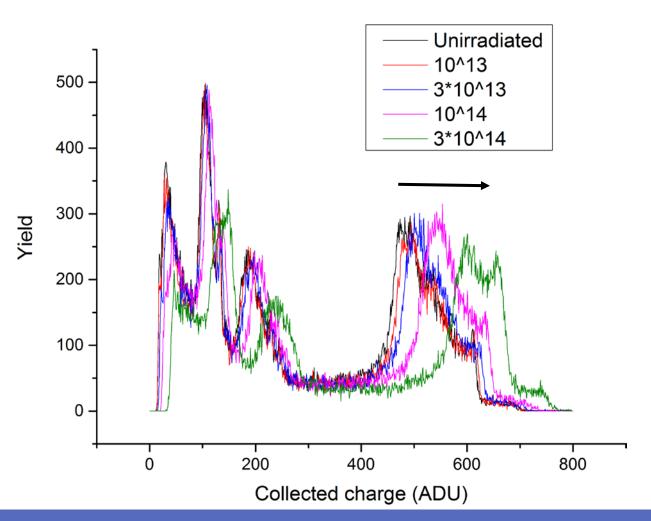


Backup

Shift of CCE





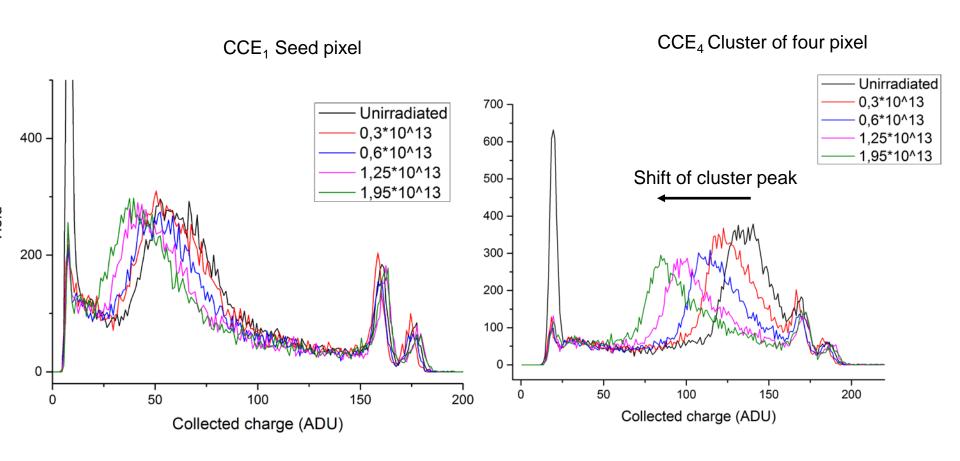


Effect also observed with Fe-55 source



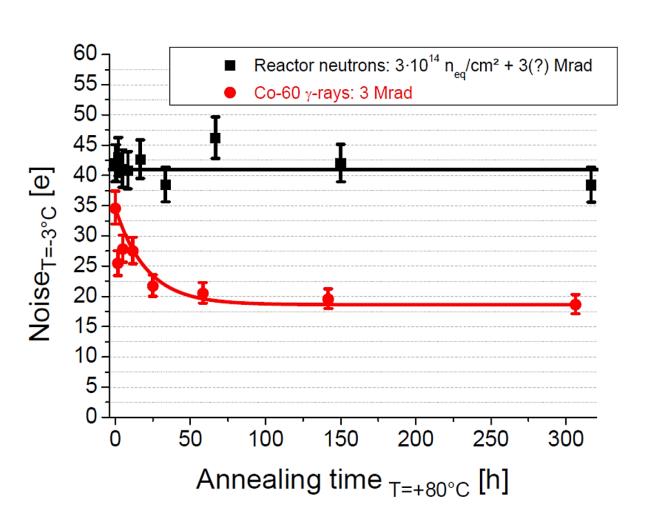


Fe⁵⁵, -3°C



Annealing parasitic ionizing radiation





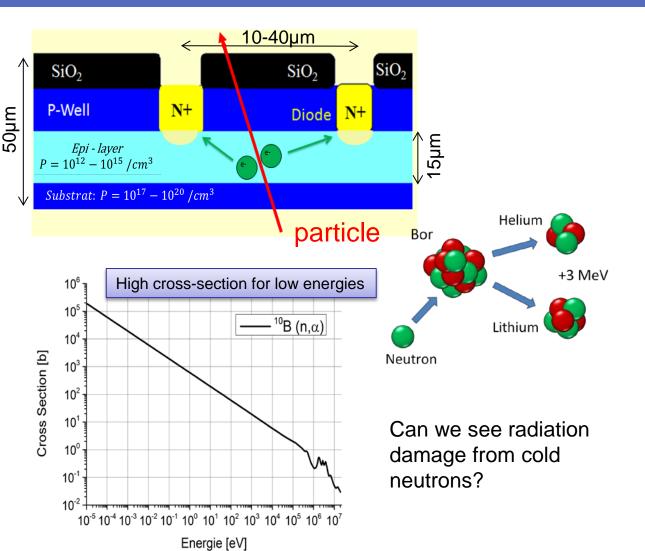
Sensor: MIMOSA-18 (AMS 0.35 HR)

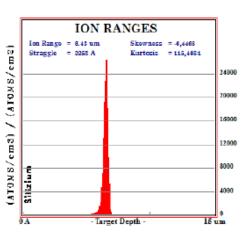
Experiment:
Irradiate sensors according to protocoll for reactor neutrons with gamma rays (not powered during irraditation)

Observation:
Gamma rays may provide significant contribution to leakage current/shot noise. This contribution is eliminated after annealing while the bulk damage persists.



Why do we have more damage then expected?





T. Bus, bachelor thesis 2015

